

MOSFET - Symmetrical Dual N-Channel

80 V, 18 mΩ, 26 A

NTTFD018N08LC

General Description

This device includes two specialized N-Channel MOSFETs in a dual package. The switch node has been internally connected to enable easy placement and routing of synchronous buck converters. The control MOSFET (Q2) and synchronous (Q1) have been designed to provide optimal power efficiency.

Features

Q1: N-Channel

- Max $r_{DS(on)} = 18 \text{ m}\Omega$ at $V_{GS} = 10 \text{ V}$, $I_D = 7.8 \text{ A}$
- Max $r_{DS(on)} = 29 \text{ m}\Omega$ at $V_{GS} = 4.5 \text{ V}$, $I_D = 6.2 \text{ A}$

Q2: N-Channel

- Max $r_{DS(on)} = 18 \text{ m}\Omega$ at $V_{GS} = 10 \text{ V}$, $I_D = 7.8 \text{ A}$
- Max $r_{DS(on)} = 29 \text{ m}\Omega$ at $V_{GS} = 4.5 \text{ V}$, $I_D = 6.2 \text{ A}$
- Low Inductance Packaging Shortens Rise/Fall Times, Resulting in Lower Switching Losses
- RoHS Compliant

Typical Applications

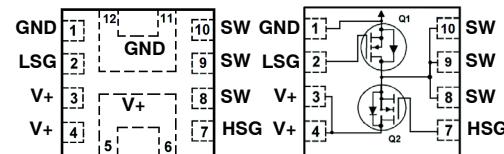
- 48 V Input Primary Half Bridge
- Communications
- General Purpose Point of Load

PIN DESCRIPTION

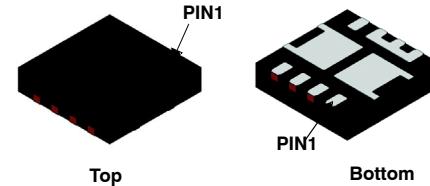
Pin	Name	Description
1, 11, 12	GND (LSS)	Low Side Source
2	LSG	Low Side Gate
3, 4, 5, 6	V + (HSD)	High Side Drain
7	HSG	High Side Gate
8, 9, 10	SW	Switching Node, Low Side Drain

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
80 V	18 mΩ @ 10 V	26 A
	29 mΩ @ 4.5 V	

ELECTRICAL CONNECTION

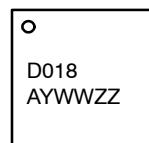


Dual N-Channel MOSFET



Power Clip 33 Symmetric
(WQFN12)
CASE 510CJ

MARKING DIAGRAM



D018 = Specific Device Code
 A = Assembly Plant Code
 Y = Numeric Year Code
 WW = Work Week Code
 ZZ = Assembly Lot Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

NTTFD018N08LC

ORDERING INFORMATION AND PACKAGE MARKING

Device	Marking	Package	Shipping [†]
NTTFD018N08LC	D018	WQFN12 (Pb-Free)	3000 Units/ Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MOSFET MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, Unless otherwise specified)

Symbol	Parameter	Q1	Q2	Units
V_{DS}	Drain to Source Voltage	80	80	V
V_{GS}	Gate to Source Voltage	± 20	± 20	V
I_D	Drain Current –Continuous $T_C = 25^\circ\text{C}$ (Note 4)	26	26	A
	–Continuous $T_C = 100^\circ\text{C}$ (Note 4)	16	16	
	–Continuous $T_A = 25^\circ\text{C}$	6 (Note 1a)	6 (Note 1b)	
	–Pulsed $T_A = 25^\circ\text{C}$	349	349	
E_{AS}	Single Pulse Avalanche Energy ($L = 1 \text{ mH}$, $I_{L(pk)} = 8 \text{ A}$) (Note 3)	32	32	mJ
P_D	Power Dissipation for Single Operation $T_C = 25^\circ\text{C}$	26	26	W
	Power Dissipation for Single Operation $T_A = 25^\circ\text{C}$	1.7 (Note 1a)	1.7 (Note 1b)	
I_S	Source Current (Body Diode)	21	21	A
T_J , T_{STG}	Operating and Storage Junction Temperature Range	$-55 \text{ to } +150$		$^\circ\text{C}$
T_L	Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	260	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Q1	Q2	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	4.8	4.8	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	70 (Note 1a)	70 (Note 1b)	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	135 (Note 1c)	135 (Note 1c)	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Type	Min.	Typ.	Max.	Units
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OFF CHARACTERISTICS

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}$, $V_{GS} = 0 \text{ V}$	Q1	80			V
		$I_D = 250 \mu\text{A}$, $V_{GS} = 0 \text{ V}$	Q2	80			
ΔBV_{DSS} ΔT_J	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, referenced to 25°C	Q1		76.81		$\text{mV}/^\circ\text{C}$
		$I_D = 250 \mu\text{A}$, referenced to 25°C	Q2		76.81		
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 64 \text{ V}$, $V_{GS} = 0 \text{ V}$	Q1			1	μA
		$V_{DS} = 64 \text{ V}$, $V_{GS} = 0 \text{ V}$	Q2			1	
I_{GSS}	Gate to Source Leakage Current, Forward	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$	Q1			± 100	μA
		$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$	Q2			± 100	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Type	Min.	Typ.	Max.	Units
ON CHARACTERISTICS							
$V_{GS(\text{th})}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 44 \mu\text{A}$	Q1	1.0	1.5	2.5	V
		$V_{GS} = V_{DS}, I_D = 44 \mu\text{A}$	Q2	1.0	1.5	2.5	
$\Delta V_{GS(\text{th})}$ ΔT_J	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 44 \mu\text{A}$, referenced to 25°C	Q1		-5.71		$\text{mV}/^\circ\text{C}$
		$I_D = 44 \mu\text{A}$, referenced to 25°C	Q2		-5.71		
$r_{DS(\text{on})}$	Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 7.8 \text{ A}$	Q1		15	18	$\text{m}\Omega$
		$V_{GS} = 4.5 \text{ V}, I_D = 6.2 \text{ A}$			22	29	
		$V_{GS} = 10 \text{ V}, I_D = 7.8 \text{ A}, T_J = 125^\circ\text{C}$			25		
$r_{DS(\text{on})}$	Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 7.8 \text{ A}$	Q2		15	18	$\text{m}\Omega$
		$V_{GS} = 4.5 \text{ V}, I_D = 6.2 \text{ A}$			22	29	
		$V_{GS} = 10 \text{ V}, I_D = 7.8 \text{ A}, T_J = 125^\circ\text{C}$			25		
g_{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_D = 7.8 \text{ A}$	Q1		23		S
		$V_{DS} = 5 \text{ V}, I_D = 7.8 \text{ A}$	Q2		23		

DYNAMIC CHARACTERISTICS

C_{ISS}	Input Capacitance	Q1: $V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ Q2: $V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	Q1		856		pF	
			Q2		856			
C_{OSS}	Output Capacitance		Q1		230		pF	
			Q2		230			
C_{RSS}	Reverse Transfer Capacitance		Q1		10		pF	
			Q2		10			
R_G	Gate Resistance	$T_A = 25^\circ\text{C}$	Q1		0.5		Ω	
			Q2		0.5			

SWITCHING CHARACTERISTICS

$t_{d(\text{ON})}$	Turn – On Delay Time	Q1: $V_{DD} = 40 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 6.2 \text{ A}, R_{\text{GEN}} = 6 \Omega$ Q2: $V_{DD} = 40 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 6.2 \text{ A}, R_{\text{GEN}} = 6 \Omega$	Q1		9.4		ns	
			Q2		9.4			
t_r	Rise Time		Q1		5.8		ns	
			Q2		5.8			
$t_{D(\text{OFF})}$	Turn – Off Delay Time		Q1		14.6		ns	
			Q2		14.6			
t_f	Fall Time		Q1		5.5		ns	
			Q2		5.5			
Q_g	Total Gate Charge	$V_{GS} = 0\text{V} \text{ to } 10 \text{ V}$	Q1		12.4		nC	
			Q2		12.4			
Q_g	Total Gate Charge	$V_{GS} = 0\text{V} \text{ to } 4.5 \text{ V}$	Q1		6.0		nC	
			Q2		6.0			
Q_{gs}	Gate to Source Gate Charge	Q1: $V_{DD} = 40 \text{ V}, I_D = 6.2 \text{ A}$ Q2: $V_{DD} = 40 \text{ V}, I_D = 6.2 \text{ A}$	Q1		1.94		nC	
			Q2		1.94			
Q_{gd}	Gate to Drain "Miller" Charge	Q1: $V_{DD} = 40 \text{ V}, I_D = 6.2 \text{ A}$ Q2: $V_{DD} = 40 \text{ V}, I_D = 6.2 \text{ A}$	Q1		1.71		nC	
			Q2		1.71			

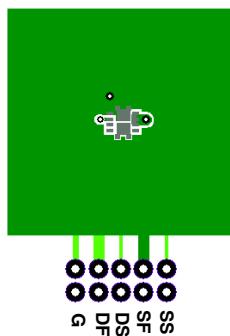
ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Type	Min.	Typ.	Max.	Units
DRAIN-SOURCE DIODE CHARACTERISTICS							
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}$, $I_S = 7.8 \text{ A}$ (Note 2)	Q1		0.82	1.5	V
		$V_{GS} = 0 \text{ V}$, $I_S = 7.8 \text{ A}$ (Note 2)	Q2		0.82	1.5	
t_{rr}	Reverse Recovery Time	Q1: $I_F = 7.8 \text{ A}$, $di/dt = 300 \text{ A}/\mu\text{s}$	Q1		13.3		ns
		Q2: $I_F = 7.8 \text{ A}$, $di/dt = 300 \text{ A}/\mu\text{s}$	Q2		13.3		
Q_{rr}	Reverse Recovery Charge	Q1: $I_F = 7.8 \text{ A}$, $di/dt = 300 \text{ A}/\mu\text{s}$	Q1		18.1		nC
		Q2: $I_F = 7.8 \text{ A}$, $di/dt = 300 \text{ A}/\mu\text{s}$	Q2		18.1		
t_{rr}	Reverse Recovery Time	Q1: $I_F = 7.8 \text{ A}$, $di/dt = 1000 \text{ A}/\mu\text{s}$	Q1		10.3		ns
		Q2: $I_F = 7.8 \text{ A}$, $di/dt = 1000 \text{ A}/\mu\text{s}$	Q2		10.3		
Q_{rr}	Reverse Recovery Charge	Q1: $I_F = 7.8 \text{ A}$, $di/dt = 1000 \text{ A}/\mu\text{s}$	Q1		51		nC
		Q2: $I_F = 7.8 \text{ A}$, $di/dt = 1000 \text{ A}/\mu\text{s}$	Q2		51		

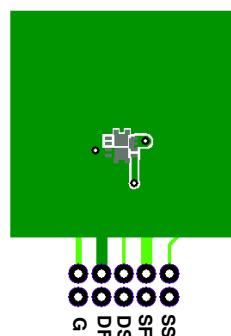
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

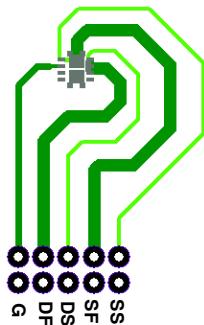
1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR-4 material. $R_{\theta CA}$ is determined by the user's board design.



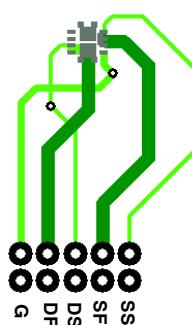
a) 70°C/W when mounted on a 1 in² pad of 2 oz copper.



b) 70°C/W when mounted on a 1 in² pad of 2 oz copper.



c) 135°C/W when mounted on a minimum pad of 2 oz copper.



d) 135°C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

3. Q1: E_{AS} of 32 mJ is based on starting $T_J = 25^\circ\text{C}$; N-ch: $L = 1 \text{ mH}$, $I_{AS} = 8 \text{ A}$, $V_{DD} = 80 \text{ V}$, $V_{GS} = 10 \text{ V}$. 100% test at $L = 1 \text{ mH}$, $I_{AS} = 8.2 \text{ A}$.
Q2: E_{AS} of 32 mJ is based on starting $T_J = 25^\circ\text{C}$; N-ch: $L = 1 \text{ mH}$, $I_{AS} = 8 \text{ A}$, $V_{DD} = 80 \text{ V}$, $V_{GS} = 10 \text{ V}$. 100% test at $L = 1 \text{ mH}$, $I_{AS} = 8.2 \text{ A}$.

4. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

TYPICAL CHARACTERISTICS

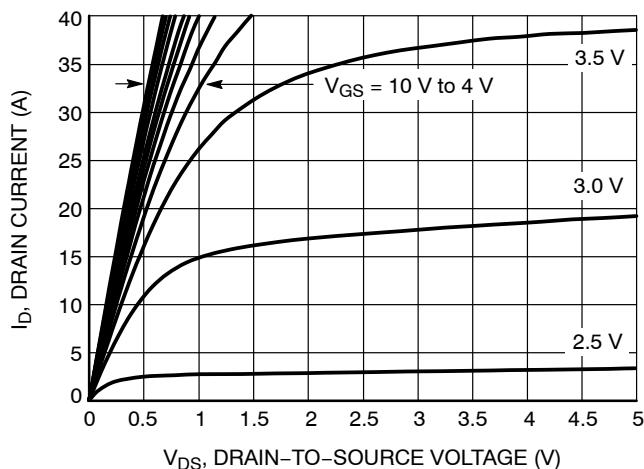


Figure 1. On-Region Characteristics

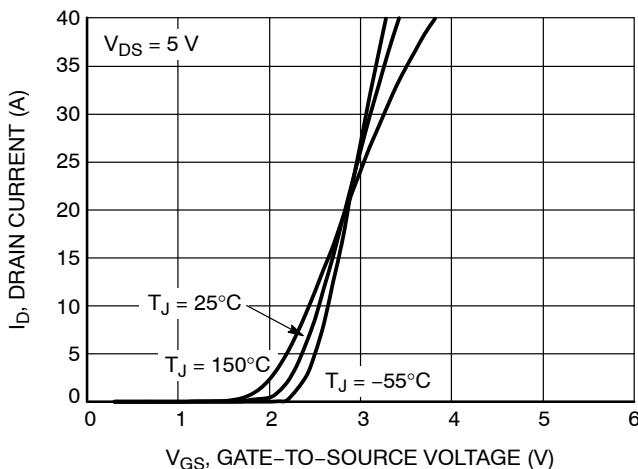


Figure 2. Transfer Characteristics

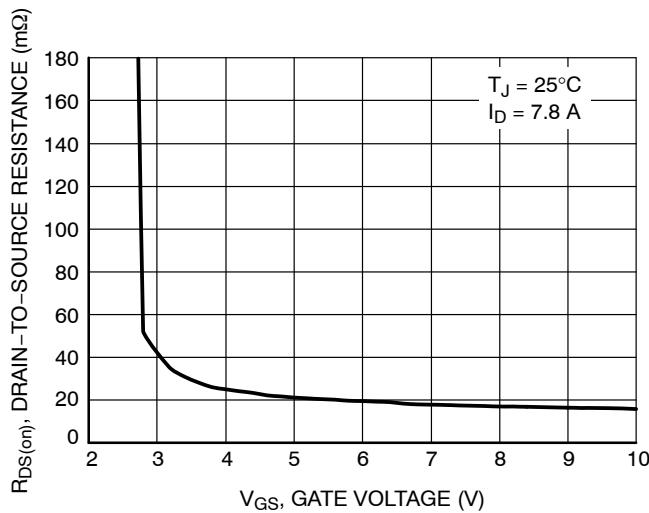


Figure 3. On-Resistance vs. Gate-to-Source Voltage

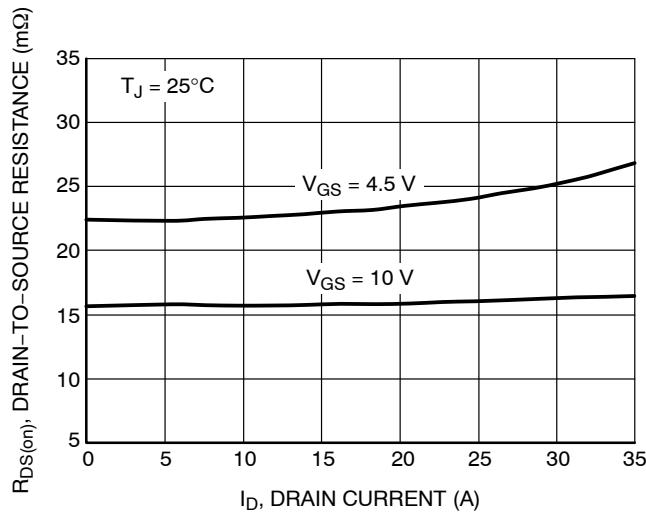


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

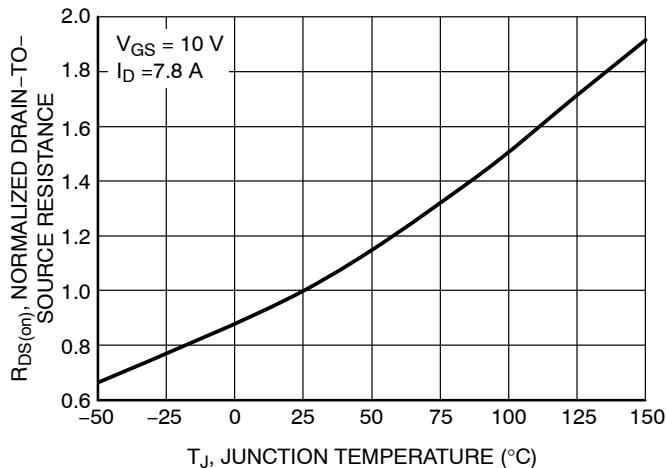


Figure 5. On-Resistance Variation with Temperature

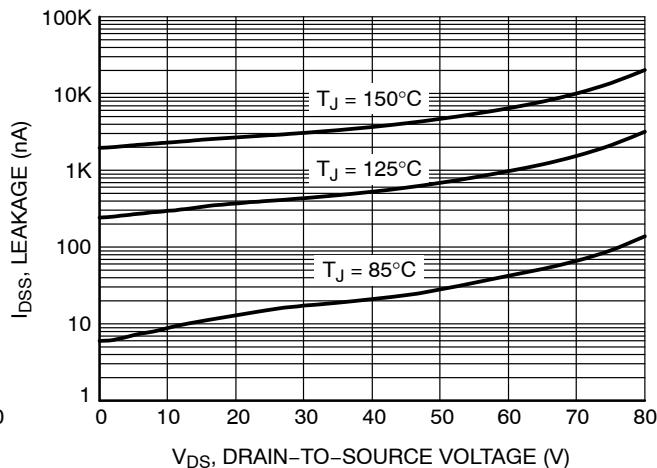


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

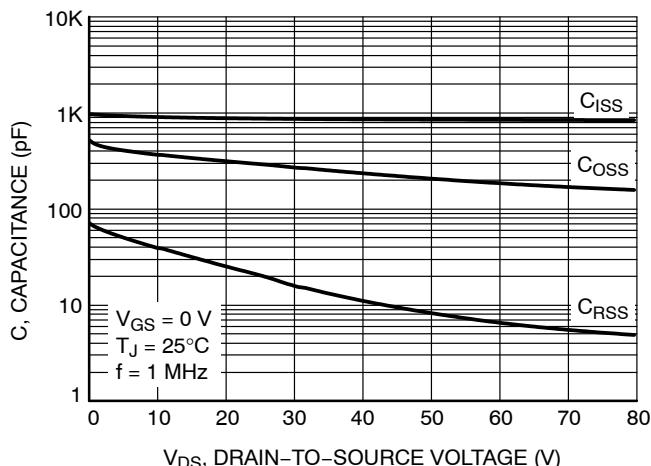


Figure 7. Capacitance Variation

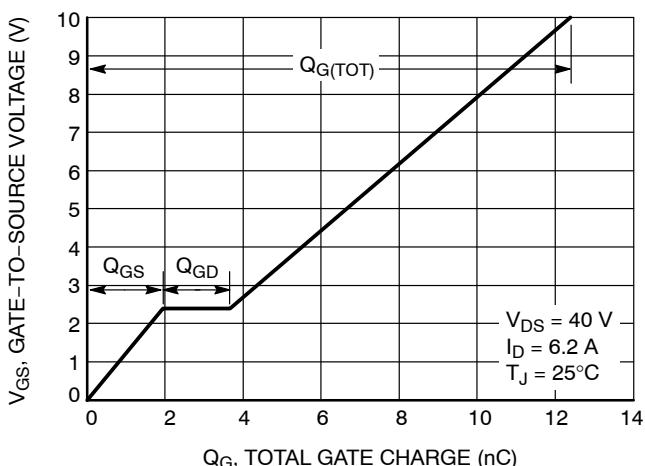


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

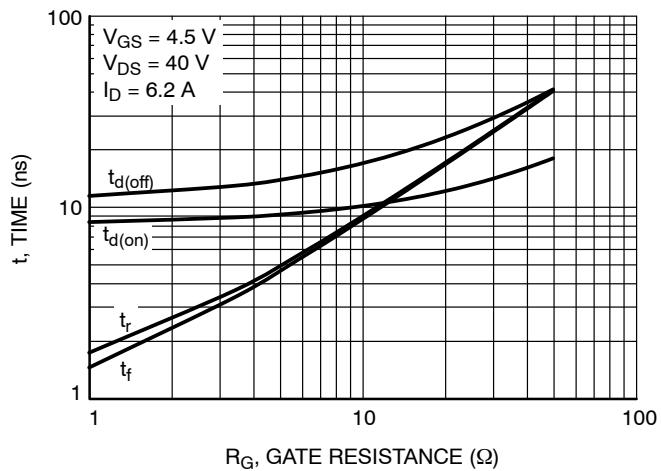


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

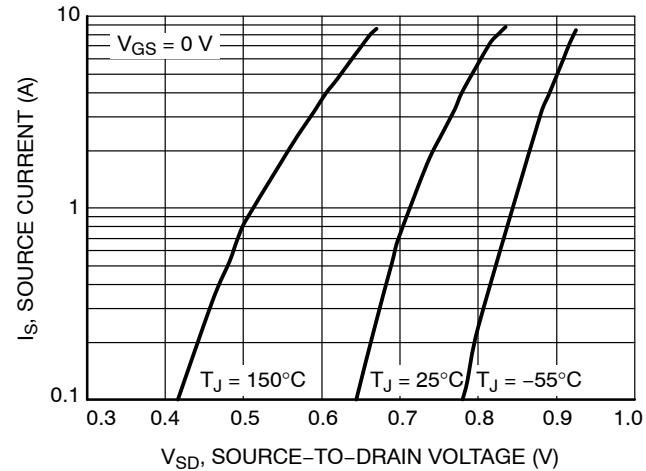


Figure 10. Diode Forward Voltage vs. Current

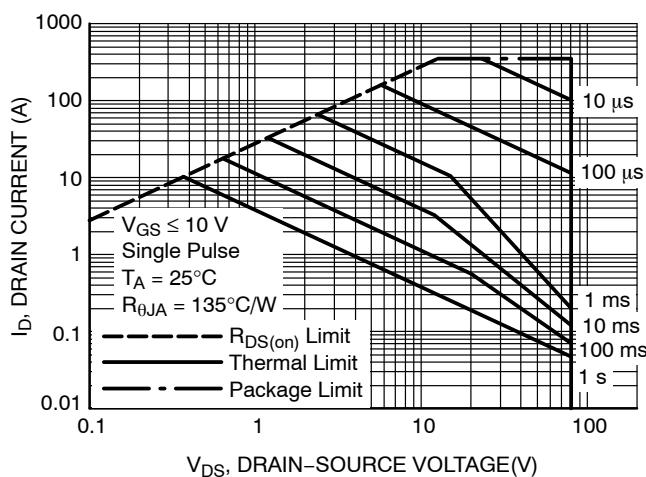
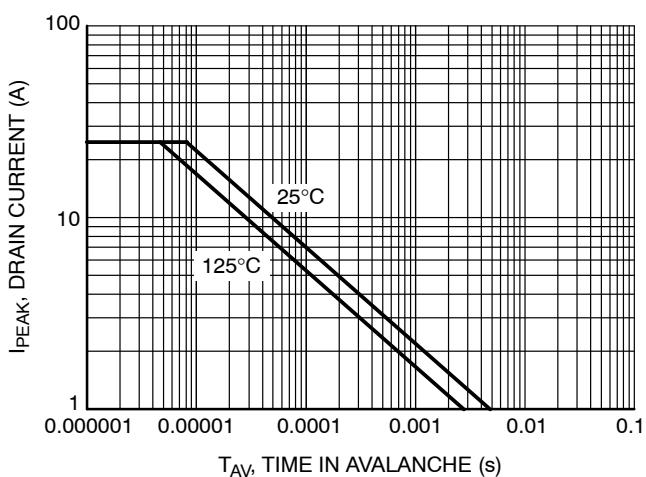


Figure 11. Safe Operating Area

Figure 12. I_{PEAK} vs. Time in Avalanche

TYPICAL CHARACTERISTICS

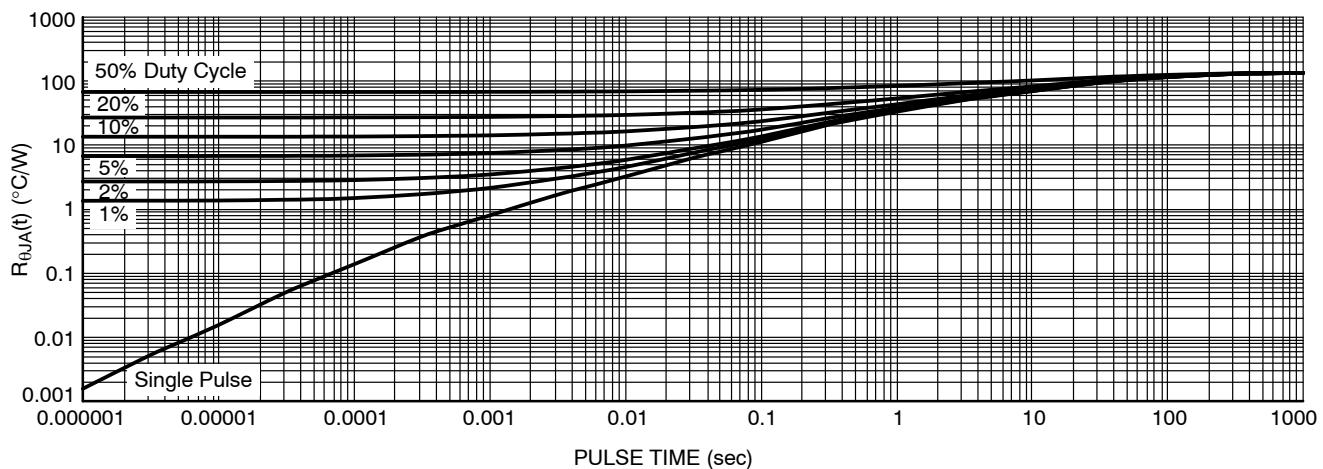


Figure 13. Thermal Characteristics

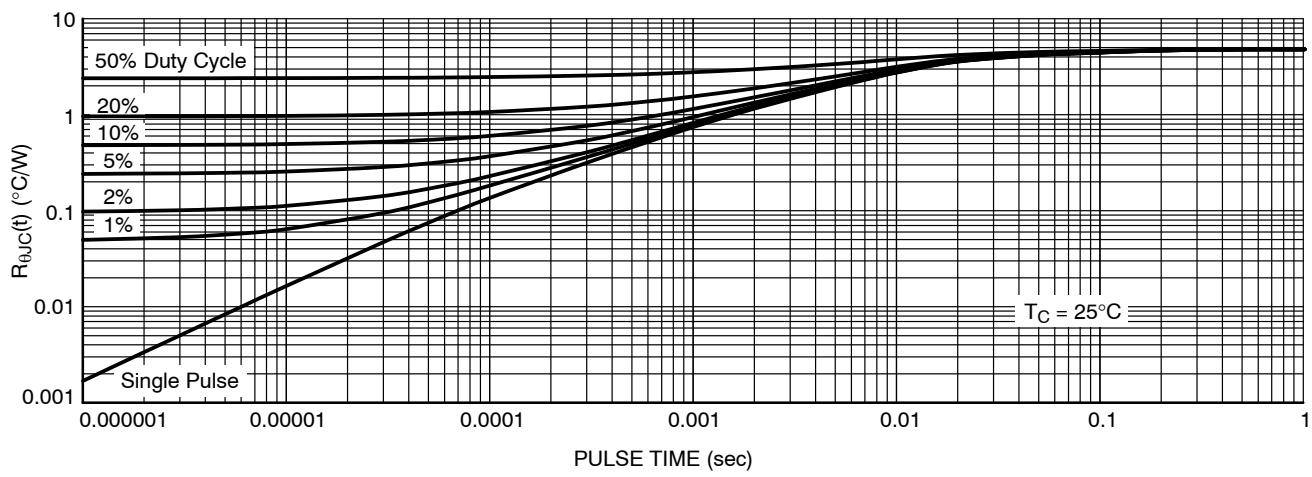
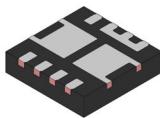
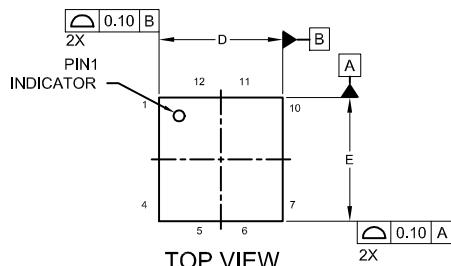


Figure 14. Thermal Characteristics



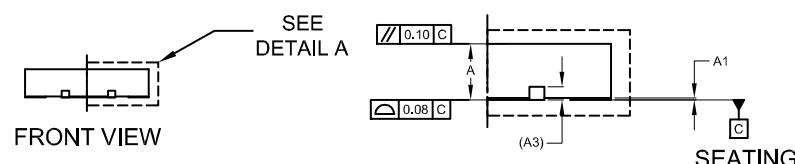
**WQFN12 3.3X3.3, 0.65P
CASE 510CJ
ISSUE A**

DATE 08 AUG 2022

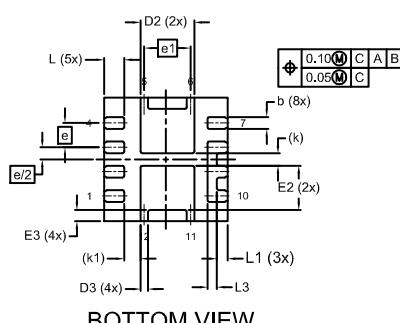


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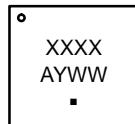
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED
4. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
5. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEFP OUT AREA



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	--	0.05
A3	0.20 REF		
b	0.27	0.32	0.37
D	3.20	3.30	3.40
D2	1.34	1.44	1.54
D3	0.10	0.20	0.30
E	3.20	3.30	3.40
E2	1.09	1.19	1.29
E3	0.20	0.30	0.40
e	0.65 BSC		
e/2	0.325 BSC		
e1	1.24 BSC		
k	0.33 REF		
k1	0.43 REF		
L	0.44	0.54	0.64
L1	0.19	0.29	0.39
L3	0.15	0.25	0.35



GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

LAND PATTERN

RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SODERRM/D.

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DESCRIPTION:	WQFN12 3.3X3.3, 0.65P	PAGE 1 OF 1

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